

BAR63...

Silicon PIN Diodes

- PIN diode for high speed switching of RF signals
- Very low forward resistance (low insertion loss)
- Very low capacitance (high isolation)
- For frequencies up to 3GHz
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101¹⁾



BAR63-02.. BAR63-03W

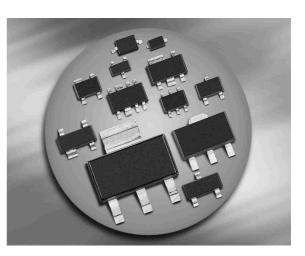
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BAR63-04 BAR63-04W



BAR63-05 BAR63-05W



BAR63-06 BAR63-06W



Туре	Package	Configuration	L _S (nH)	Marking
BAR63-02L*	TSLP-2-1	single, leadless	0.4	G
BAR63-02V	SC79	single	0.6	G
BAR63-02W	SCD80	single	0.6	GG
BAR63-03W	SOD323	single	1.8	white G
BAR63-04	SOT23	series	1.8	G4s
BAR63-04W	SOT323	series	1.4	G4s
BAR63-05	SOT23	common cathode	1.8	G5s
BAR63-05W	SOT323	common cathode	1.4	G5s
BAR63-06	SOT23	common anode	1.8	G6s
BAR63-06W	SOT323	common anode	1.4	G6s

¹*BAR63-02L is not qualified according AEC Q101



Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit V	
Diode reverse voltage	V _R	50		
Forward current	/ _F	100	mA	
Total power dissipation	P _{tot}		mW	
BAR63-02L, <i>T</i> _S ≤ 118°C		250		
BAR63-02V, -02W, BAR63-03W, <i>T</i> _S ≤ 115°C		250		
BAR63-04BAR63-06 <i>, T</i> S ≤ 55°C		250		
BAR63-04S <i>, T</i> _S ≤ 115°C		250		
BAR63-04WBAR63-06W, $T_{S} \le 105^{\circ}C$		250		
Junction temperature	T _i	150	°C	
Operating temperature range	T _{op}	-55 125		
Storage temperature	T _{stq}	-55 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BAR63-02L		≤ 125	
BAR63-02V, BAR63-02W		≤ 140	
BAR63-03W		≤ 155	
BAR63-04BAR63-06		≤ 380	
BAR63-04S		≤ 180	
BAR63-04WBAR63-06W		≤ 180	

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	·	·			
Breakdown voltage	V _(BR)	50	-	-	V
I _(BR) = 5 μA					
Reverse current	I _R	-	-	10	nA
<i>V</i> _R = 35 V					
Forward voltage	V _F	-	0.95	1.2	V
<i>I</i> _F = 100 mA					

¹For calculation of $R_{\rm thJA}$ please refer to the Technical Information



Parameter	Symbol		Values			
		min.	typ.	max.	<u> </u>	
AC Characteristics				-		
Diode capacitance	CT				pF	
$V_{R} = 5 V, f = 1 MHz$		-	0.21	0.3		
<i>V</i> _R = 0 V, 100 MHz 1.8 GHz		-	0.3	-		
Reverse parallel resistance	R _P				kΩ	
V _R = 0 V, <i>f</i> = 100 MHz		-	500	-		
V _R = 0 V, <i>f</i> = 1 GHz		-	15	-		
V _R = 0 V, <i>f</i> = 1.8 GHz		-	5	-		
Forward resistance	r _f				Ω	
<i>I</i> _F = 5 mA, <i>f</i> = 100 MHz		-	1.2	2		
<i>I</i> _F = 10 mA, <i>f</i> = 100 MHz		-	1	-		
Charge carrier life time	τ _{rr}	-	75	-	ns	
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 6 mA, measured at $I_{\rm R}$ = 3 mA,						
<i>R</i> _L = 100 Ω						
I-region width	W	-	4.5	-	μm	
Insertion loss ¹⁾	/L				dB	
<i>I</i> _F = 1 mA, <i>f</i> = 1.8 GHz		-	0.15	-		
<i>I</i> _F = 5 mA, <i>f</i> = 1.8 GHz		-	0.11	-		
<i>I</i> _F = 10 mA, <i>f</i> = 1.8 GHz		-	0.1	-		
Isolation ¹⁾	I _{SO}				1	
V _R = 0 V, <i>f</i> = 0.9 GHz		-	17.9	-		
V _R = 0 V, <i>f</i> = 1.8 GHz		-	12.3	-		
<i>V</i> _R = 0 V, <i>f</i> = 2.45 GHz		-	10	-		
Series inductance	L _S	-	-	-		

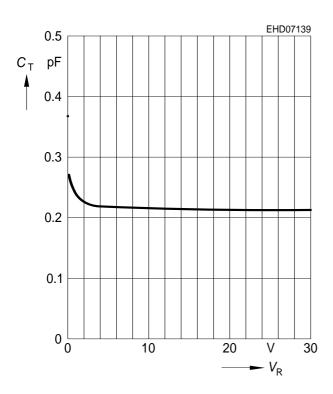
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

¹BAR63-02L in series configuration, $Z = 50\Omega$



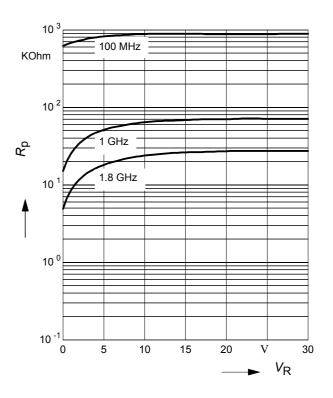
Diode capacitance $C_{T} = f(V_{R})$

f = 1MHz - 1.8GHz



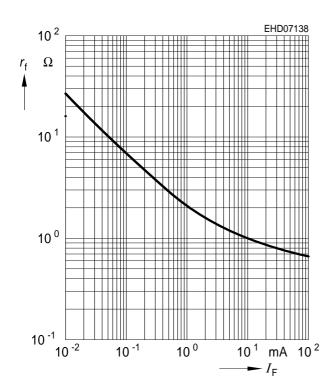
Reverse parallel resistance $R_{\rm P}$ = $f(V_{\rm R})$

f = Parameter

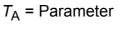


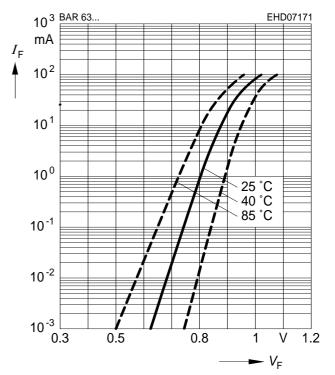
Forward resistance $r_{\rm f} = f (I_{\rm F})$

f = 100MHz



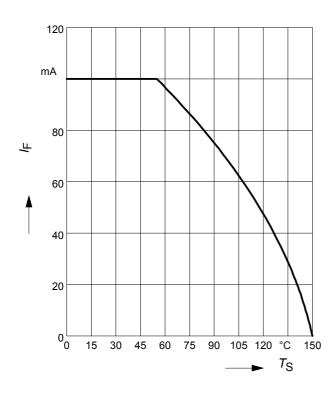
Forward current $I_{\rm F} = f(V_{\rm F})$



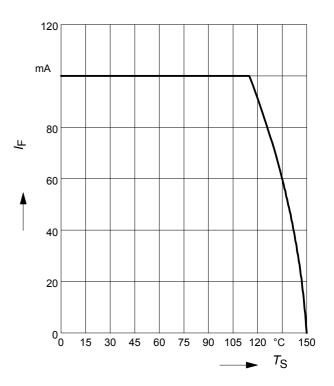




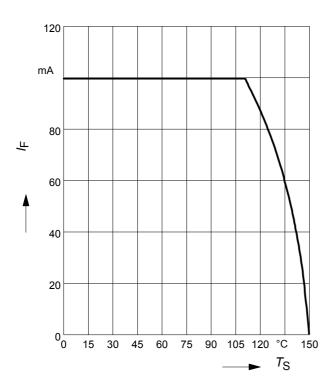
Forward current $I_F = f(T_S)$ BAR63-04...BAR63-06



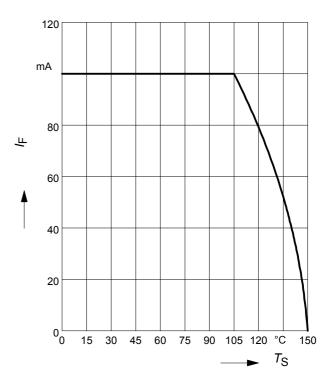
Forward current $I_F = f(T_S)$ BAR63-02V, BAR63-02W



Forward current $I_F = f(T_S)$ BAR63-03W



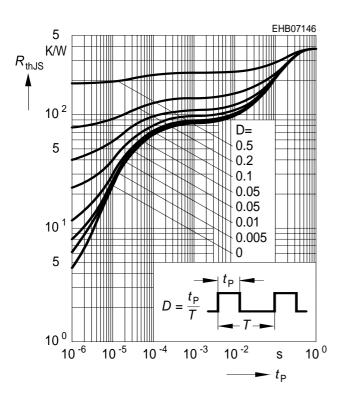
Forward current $I_F = f(T_S)$ BAR63-04W...BAR63-06W



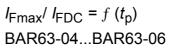


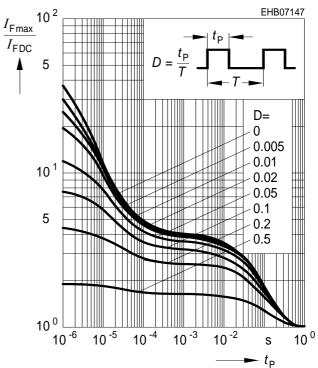
Permissible Puls Load R_{thJS} = $f(t_p)$

BAR63-04...BAR63-06

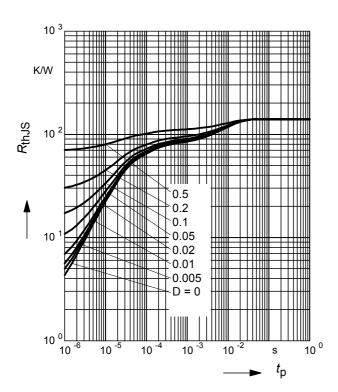


Permissible Pulse Load



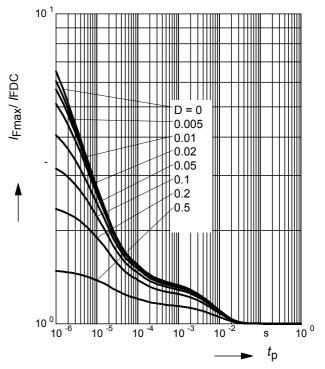


Permissible Puls Load $R_{\text{thJS}} = f(t_p)$ BAR63-02V, BAR63-02W



Permissible Pulse Load

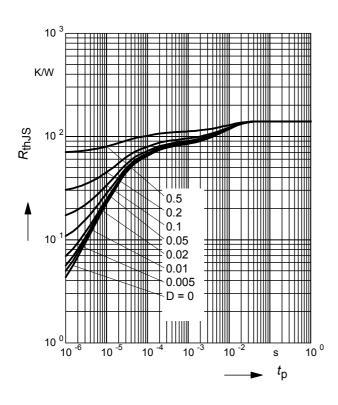
 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAR63-02V, BAR63-02W



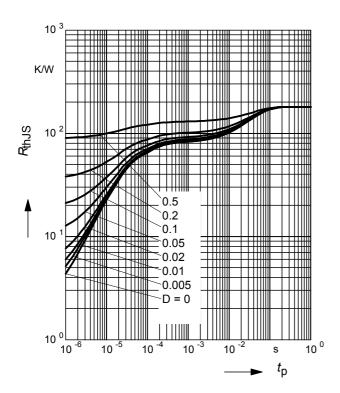


Permissible Puls Load R_{thJS} = $f(t_p)$

BAR63-03W



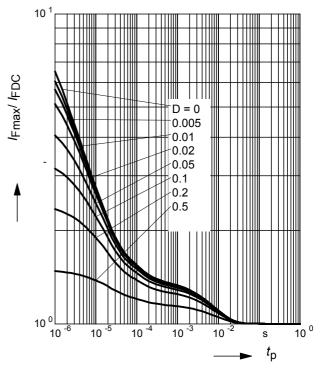
Permissible Puls Load $R_{\text{thJS}} = f(t_p)$ BAR63-04W...BAR63-06W



Permissible Pulse Load

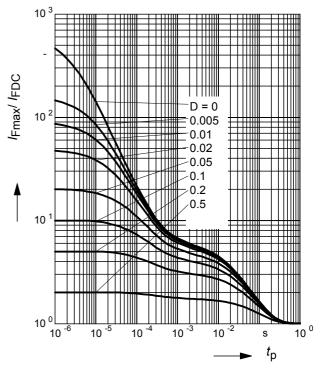
 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$

BAR63-03W



Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAR63-04W...BAR63-06W

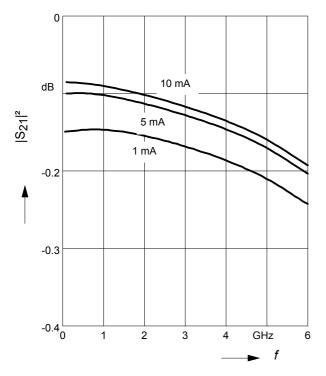




Insertion loss $I_{L} = -|S_{21}|^2 = f(f)$

 $I_{\rm F}$ = Parameter

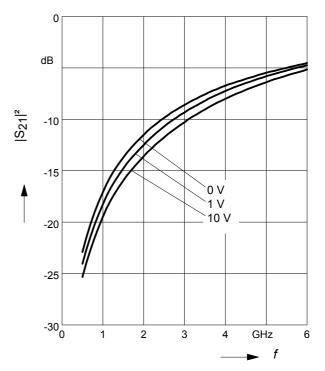
BAR63-02L in series configuration, $Z = 50\Omega$



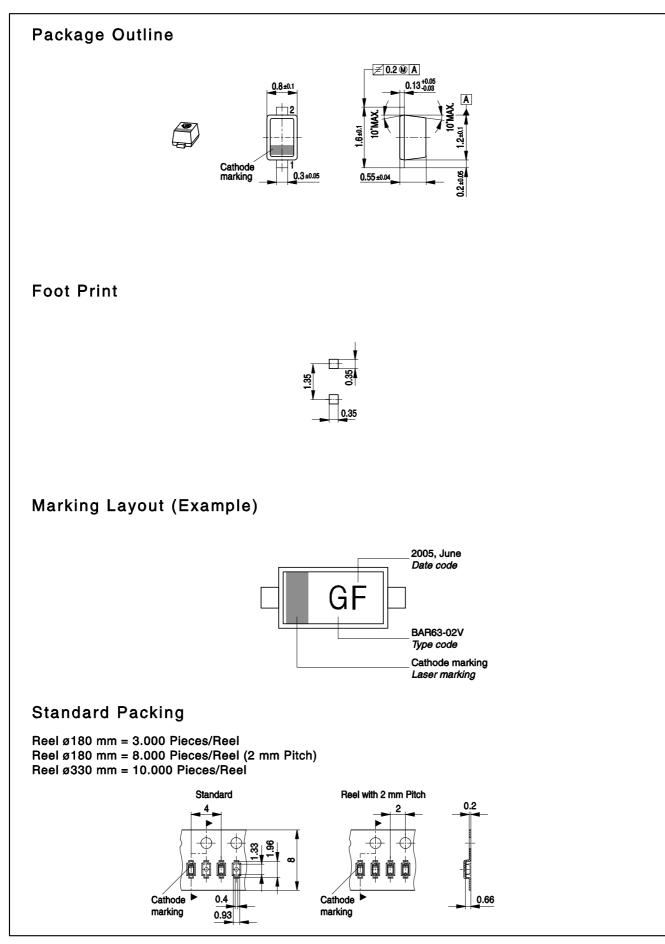
Isolation $I_{SO} = -|S_{21}|^2 = f(f)$

 $V_{\rm R}$ = Paramter

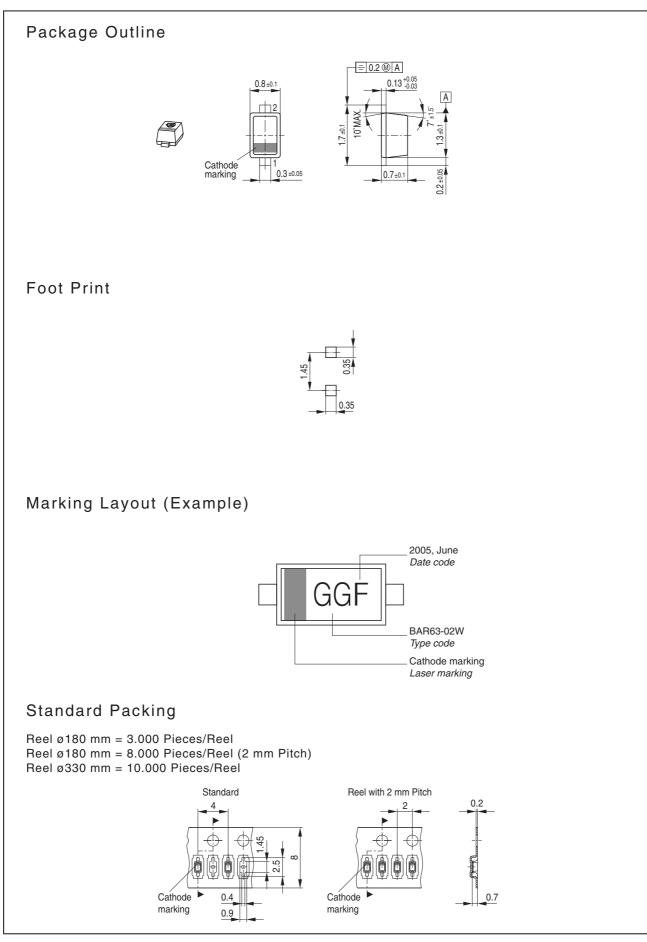
BAR63-02L in series configuration, $Z = 50\Omega$











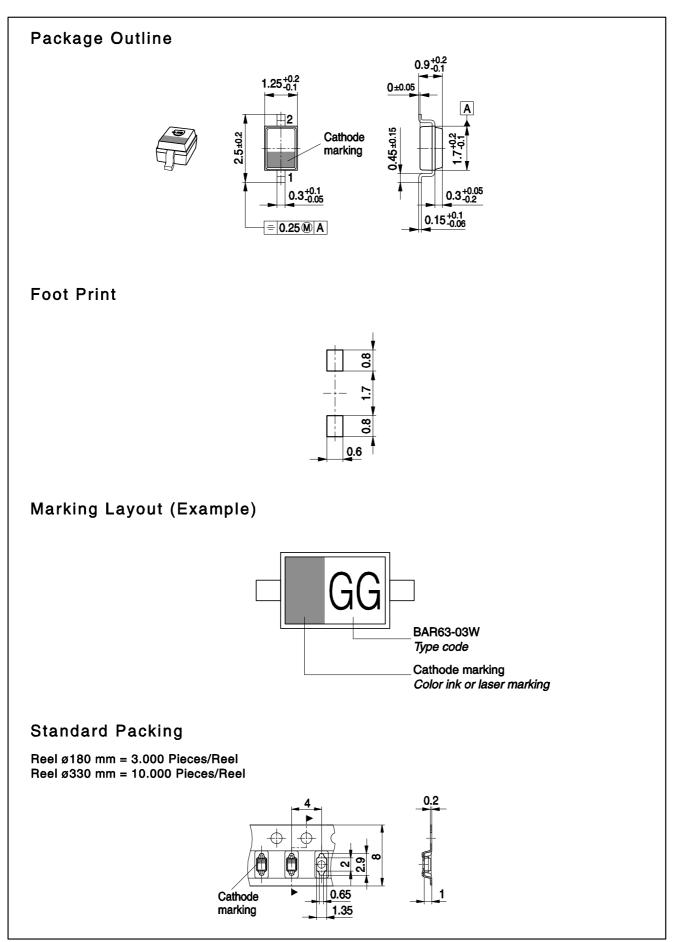


Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

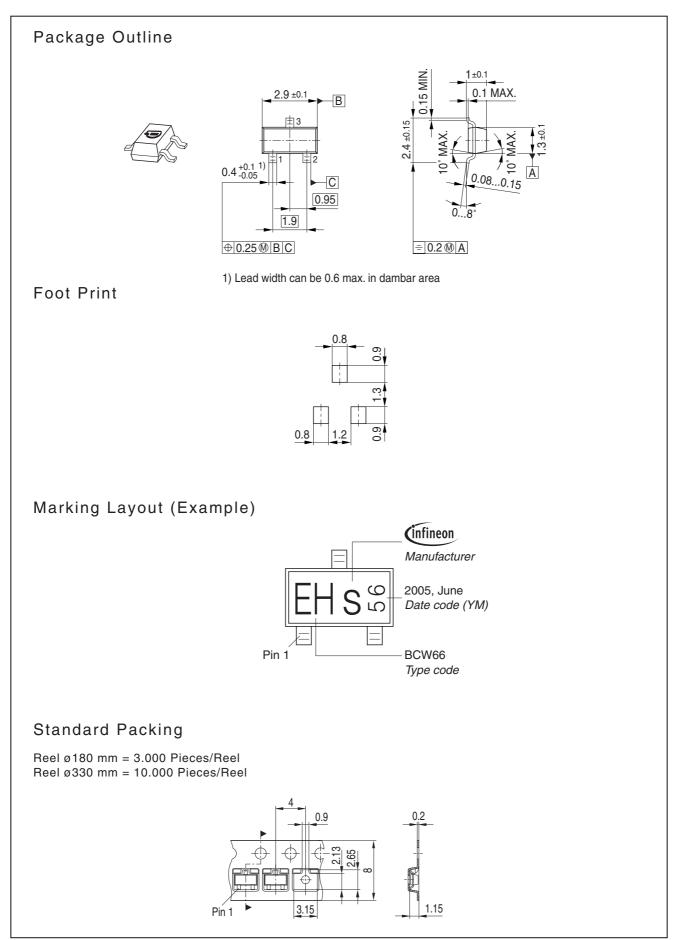
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	А	Ρ	а	р	А	Р	а	р	А	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	С	r	С	R	С	r	С	R	С	r	С	R
04	d	S	D	S	d	S	D	S	d	S	D	S
05	е	t	E	Т	е	t	E	Т	е	t	Е	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	V	G	V	g	V	G	V	g	V	G	V
08	h	х	Н	Х	h	х	Н	Х	h	х	Н	Х
09	j	у	J	Y	j	у	J	Y	j	у	J	Y
10	k	Z	K	Z	k	Z	K	Z	k	Z	K	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	Ν	5	n	3	Ν	5	n	3	Ν	5

1) New Marking Layout for SC75, implemented at October 2005.

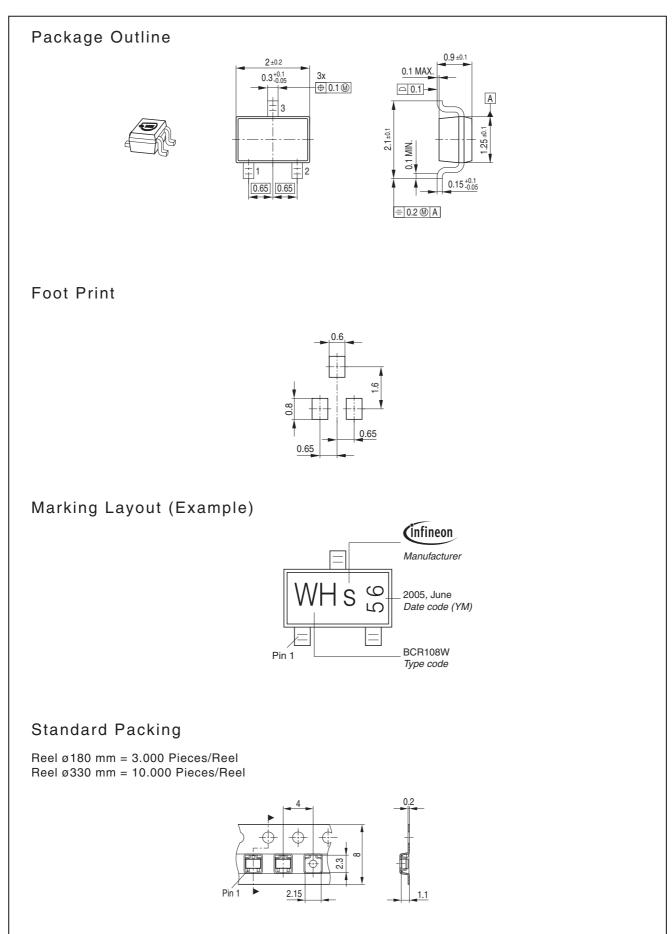




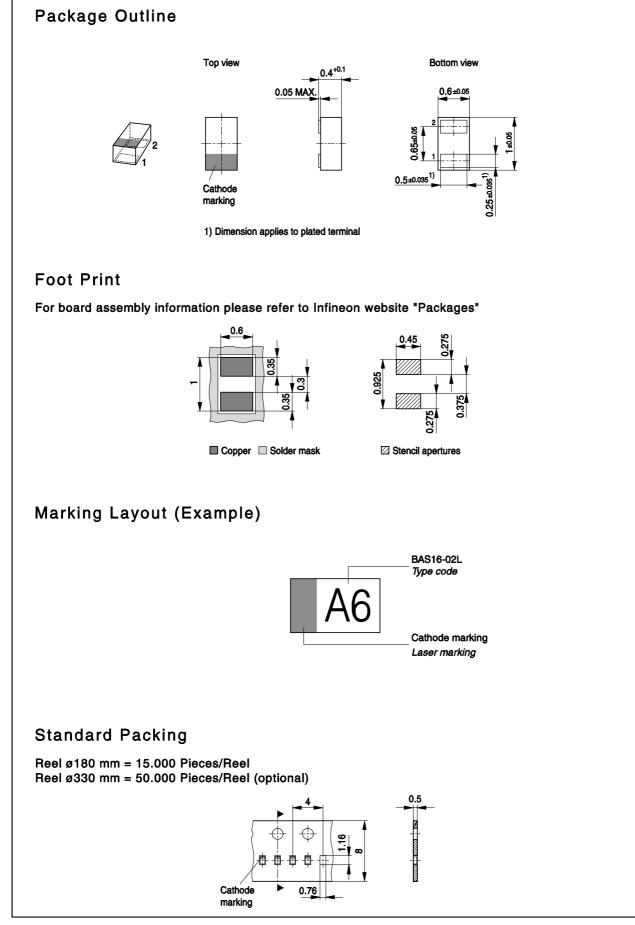
















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